SOT23 NPN SILICON PLANAR MEDIUM POWER TRANSISTORS

SUMMARY

 $V_{(BR)CEO} > 80V$

 $I_{C(cont)} = 500 \text{ mA}$

DESCRIPTION

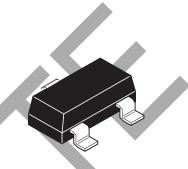
80V medium power NPN transistor in a compact SOT23 package

FEATURES

- 80V V_{CEO}
- Compact SOT23 package
- H_{FE} 50 @ I_{C} = 100 mA

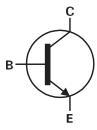
APPLICATIONS

• Low power motor driving circuits



SOT23

SYMBOL

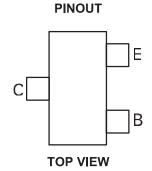


ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
FMMTA06TA	7 "	8 mm	3,000

DEVICE MARKING

1G





ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Collector-base voltage	V _{CBO}	80	V
Collector-emitter voltage	V _{CEO}	80	V
Emitter-base voltage	V _{EBO}	4	V
Peak pulse current	I _{CM}	1	A
Continuous collector current	С	500	mA
Base current	I _B	100	mA
Power dissipation @ T _A = 25° C	P _D	330	mW
Linear derating factor		2.64	mW/° C
Operating and storage temperature	Γ _j ;Τ _{st g}	-55 to + 150	°C

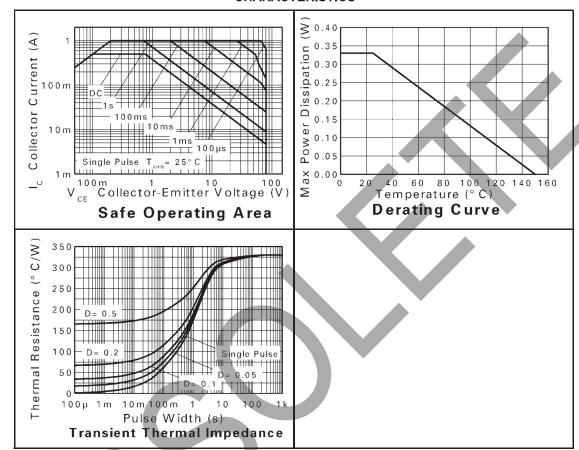
THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to ambient	R0 _{JA}	379	° C/W





CHARACTERISTICS





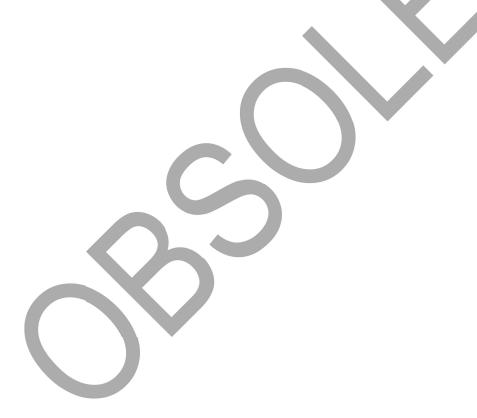


ELECTRICAL CHARACTERISTICS(at T_{amb} = 25° C unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Collector-base breakdown voltage	V _{(BR)CBO}	80			V	I _C = 1 mA
Collector-emitter breakdown voltage	/ _{(BR)CEO}	80			V	I _C = 10 mA*
Emitter-base breakdown voltage	V _{(BR)EBO}	4			V	I _E = 100 A
Collector-emitter cut-off current	CES			100	nA	V _{CES} = 60V
Collector-base cut-off current	I _{СВО}			100	nA	V _{CB} = 80V
Static forward current transfer ratio	H FE	50	120			I _C = 10 mA, V _{CE} = 1V*
		50				I _C = 100 mA, V _{CE} = 1V*
Collector-emitter saturation voltage	/ _{CE(sat)}			0.25	V	I _C = 100 mA, I _B = 10 mA*
Base-emitter turn-on voltage	V _{BE(on)}			1.2	>	I _C = 0.1A, V _{CE} = 1V*
Transition frequency	f _T	100				I _C = 10 mA, V _{CE} = 2V, f= 100 MHz

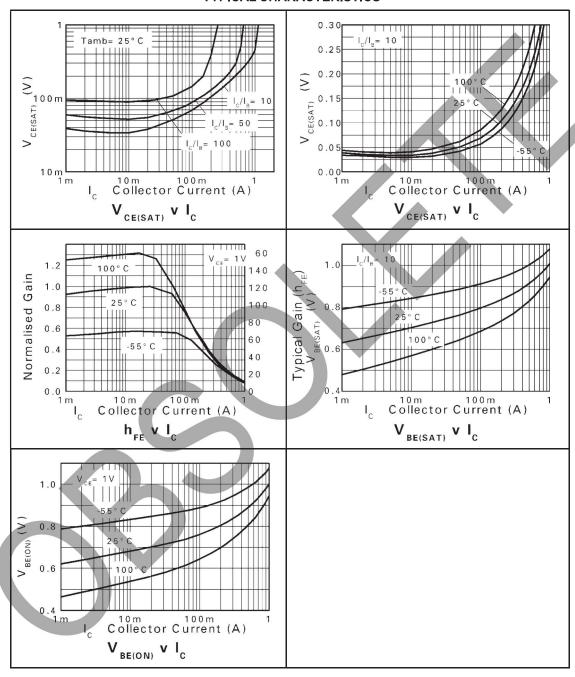
NOTES

^{*} Measured under pulsed conditions. Pulse width= 300 S. Duty cycle <2%





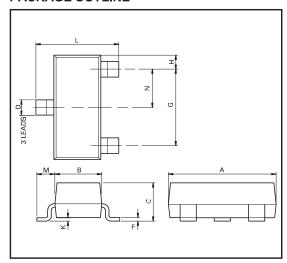
TYPICAL CHARACTERISTICS



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PACKAGE OUTLINE



Controlling dimensions are in millimeters. Approximate conversions are given in inches

PACKAGE DIMENSIONS

	Millin	neters	Inc	hes		Millimeters		Inches	
DIM	Min	Max	Min	Max	DIM	Min	Max	Max	Max
Α	2.67	3.05	0.105	0.120	Н	0.33	0.51	0.013	0.020
В	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
С		1.10		0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95	NOM	0.0375	NOM
G	1.90	NOM	0.075	NOM					

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